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Study of the effects of rapid thermal annealing in generation–recombination noise in MBE grown GaN thin films

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<b>J. Berntgen, A. Behres, J. Kluth, K. Heime, W. Daumann, U. Auer and F.-J. Tegude</b>	1911 Hooge parameter of InGaAs bulk material and InGaAs 2DEG quantum well structures based on InP substrates
<b>J. C. Vildeuil, M. Valenza and D. Rigaud</b>	1915 Low frequency noise in gate and drain of PHEMT's and related correlation
<b>M. Tacano, M. Ando, I. Shibusaki, S. Hashiguchi, J. Sikula and T. Matsui</b>	1921 Dependence of Hooge parameter of InAs heterostructure on temperature
<b>X. Y. Chen, A. Pedersen, O. G. Hellesø and A. D. van Rheezen</b>	1925 Electrical noise of laser diodes measured over a wide range of bias currents
<b>F. Principato and G. Ferrante</b>	1929 Experimental determination of the kurtosis of RF noise in microwave low-noise devices
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<b>K. Takagi, S. Serikawa and A. Okuno</b>	1943 1/f phase noise in a transistor and its application to reduce the frequency fluctuation in an oscillator
<b>T. González, J. Mateos, D. Pardo, O. M. Bulashenko and L. Reggiani</b>	1951 Effect of dimensionality on shot-noise suppression in nondegenerate diffusive conductors
<b>S. Di Pascoli and G. Iannaccone</b>	1955 Simulation of electromigration noise in polycrystalline metal stripes
<b>VI. MISCELLANEOUS</b>	
<b>O. Marinov</b>	1959 The low frequency noise in HFETs estimates the effect of electrical stress
<b>A. Godoy, J. A. Jiménez-Tejada, A. Palma and J. E. Carceller</b>	1965 Optimum design in a JFET for minimum generation-recombination noise
<b>F. Principato and G. Ferrante</b>	1969 Skewness and kurtosis of 1/f noise in semiconductor devices
<b>J. Briaire and L. K. J. Vandamme</b>	1975 The influence of a digital spectrum analyzer on the uncertainty in 1/f noise parameters

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<b>K. P. Cheung</b>	1981 Plasma-charging damage in ultra-thin gate oxide
<b>Y. Wu, Q. Xiang, J. Y. M. Yang, G. Lucovsky and M.-R. Lin</b>	1987 Time-dependent dielectric wearout technique with temperature effect for reliability test of ultrathin (<2.0 nm) single layer and dual layer gate oxides
<b>V. V. Belyakov, A. I. Chumakov, A. Y. Nikiforov, V. S. Pershenkov, P. K. Skorobogatov and A. V. Sogoyan</b>	1997 IC's radiation effects modeling and estimation
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<b>C. Lee, J.-S. Kim, H. Shin, Y.-J. Park and H.-S. Min</b>	2019 A new hole mobility model for hydrodynamic simulation
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<b>A. Paskaleva and E. Atanassova</b>	2033 Bulk oxide charge and slow states in Si-SiO <sub>2</sub> structures generated by RIE-mode plasma
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**T. M. Korhonen, D. D. Brown and M. A. Korhonen** 2053 A grain structure based statistical simulation of electromigration damage in chip level interconnect lines

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**G. Hanreich, J. Nicolics and L. Musiejovsky** 2069 High resolution thermal simulation of electronic components

**M. Amagai** 2077 The effect of polyimide surface chemistry and morphology on critical stress intensity factor

**I. V. Vasil'cov and B. A. Mandziy** 2087 Estimation of the reliability of digital systems implemented on programmable devices

**A. A. Ismaeel, R. Bhatnagar and R. Mathew** 2095 Concurrent testing in high level synthesis

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**A. Srivastava** 2111 Total dose response studies of n-channel SOI MOSFETs for low power CMOS circuits

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**L. Qi, J. Shi, H. Li, E. Jin and D. Gao** 2123 The peaks in the electric derivative curves and optic derivative curves of GaAs/GaAlAs high-power QW lasers

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